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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE *Harrison*

Application Serial No. . . . . 09/388,826  
Filing Date . . . . . September 1, 1999  
Inventor . . . . . Weimin Li et al.  
Assignee . . . . . Micron Technology, Inc.  
Group Art Unit . . . . . 2813  
Examiner . . . . . E. Kielin  
Attorney's Docket No. . . . . MI22-1208  
Title: Low k Interlevel Dielectric Layer Fabrication Methods

**RESPONSE TO JULY 25, 2000 OFFICE ACTION**

To: Box Non-Fee Amendment  
Assistant Commissioner for Patents  
Washington, D.C. 20231

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Responsive to the Office Action dated July 25, 2000, Applicant amends and remarks as follows [unless otherwise indicated, deletions are bracketed, additions are underlined]:

**AMENDMENTS**

**In the Specification:**

Page 2, line ~~15~~, change the previously amended language "at an exemplary" to --and at an exemplary--.

Page 12, line ~~4~~, change "a whole of all" to --the whole or all--.